

3A 40V(1.54mm)

**Chip Information**

Chip Size	1.54 x 1.54mm
Pad Size	1.40 x 1.40mm
Chip Quantity	4616 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al-Ni-Au (For Solder)

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR		V	
Average Forward Rectified Current	IF(AV)	3	A	
Peak Forward Surge Current	IFSM	80	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

**ELECTRICAL CHARACTERISTICS**

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition	
Maximum Forward Voltage	VF1	0.480		0.435	V	IF=3A Ta=25degC	
	VF2				V		
	VF3				V		
	VF4				V		
	VF5				V		
Maximum DC Reverse Current	IR1	0.3	0.2	0.013	mA	VR=40V Ta=25degC	
	IR2				mA		VR=40V Ta=100deg
	IR3				mA		
	IR4				mA		
Reverse Breakdown Voltage	BV	42	44	55	V	IR=0.1mA	
Junction Capacitance	Cj				pF		
Reverse Recovery Time	trr				nS		

**Ordering Information**

Chip Type	Chip Thickness	Back metal
XHJ542	250 +/- 20um	Ti-Ni-Au (For Solder)

Note:  
Designed For SB340